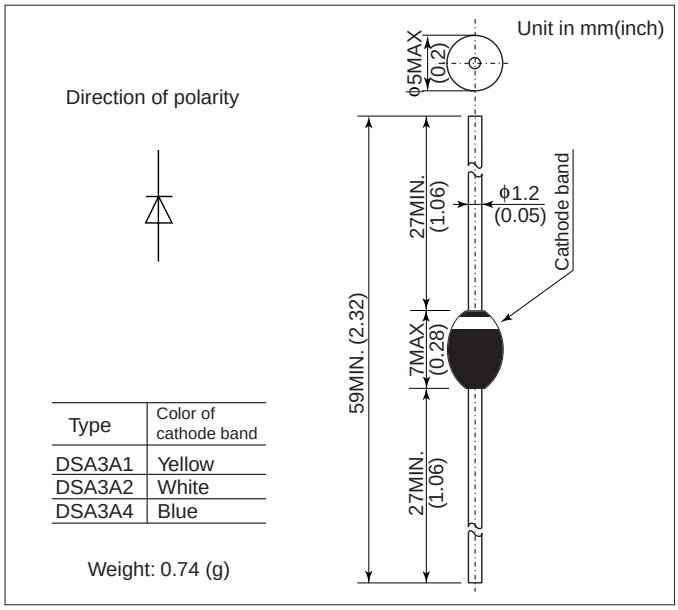
DSA3A

FEATURES

- For general purpose.
- Diffused-junction. Resin encapsulated.

OUTLINE DRAWING



Type	Color of cathode band
DSA3A1	Yellow
DSA3A2	White
DSA3A4	Blue

Weight: 0.74 (g)

ABSOLUTE MAXIMUM RATINGS

Items	Type		DSA3A1	DSA3A2	DSA3A4
Repetitive Peak Reverse Voltage	V_{RRM}	V	100	200	400
Average Forward Current	$I_{F(AV)}$	A	3.0 (Single-phase half sine wave 180° conduction, TL = 90°C, Lead length = 10mm)		
Surge(Non-Repetitive) Forward Current	I_{FSM}	A	120(Without PIV, 10ms conduction, Tj = 150°C start)		
I^2t Limit Value	I^2t	A^2s	57.6(Time = 2 ~ 10ms, I = RMS value)		
Operating Junction Temperature	T_j	°C	-40 ~ +150		
Storage Temperature	T_{stg}	°C	-40 ~ +150		

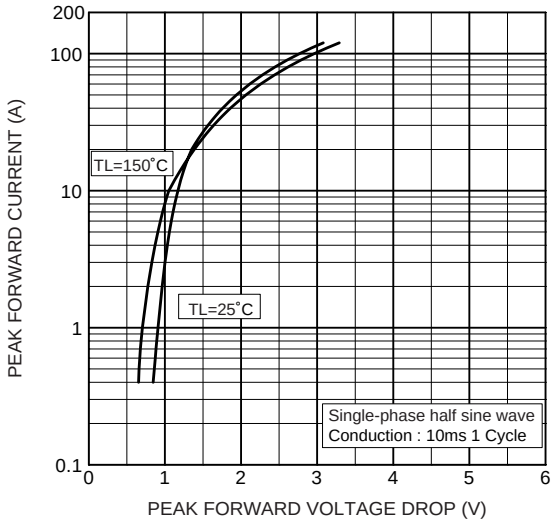
Notes (1) Lead mounting : Lead temperature 280°C max. to 3.2mm from body for 5sec. max..
(2) Mechanical strength : Bending 90°×2 cycles or 180°×1 cycle, Tensile 3kg, Twist 90°×1 cycle.

CHARACTERISTICS(T_L=25°C)

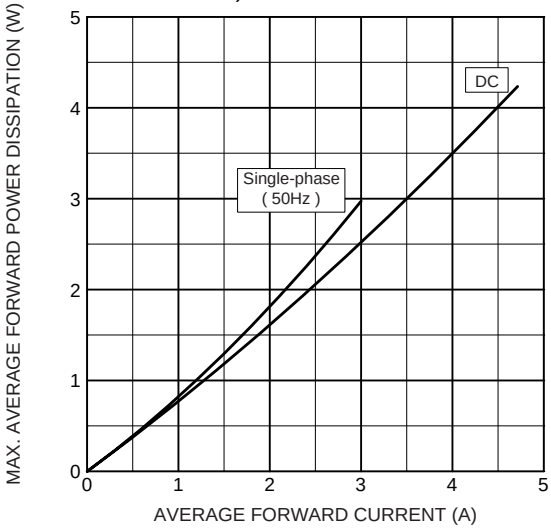
Items	Symbols	Units	Min.	Typ.	Max.	Test Conditions	
Peak Reverse Current	I_{RRM}	μA	—	—	60	DSA3A1,2	Rated V_{RRM}
					10	DSA3A 4	
Peak Forward Voltage	V_{FM}	V	—	—	1.0	I_{FM}=3.0Ap, Single-phase half sine wave 1 cycle	
Steady State Thermal Impedance	$R_{th(j-a)}$	°C/W	—	—	50	Lead length = 10 mm	
	$R_{th(j-l)}$				20		

DSA3A

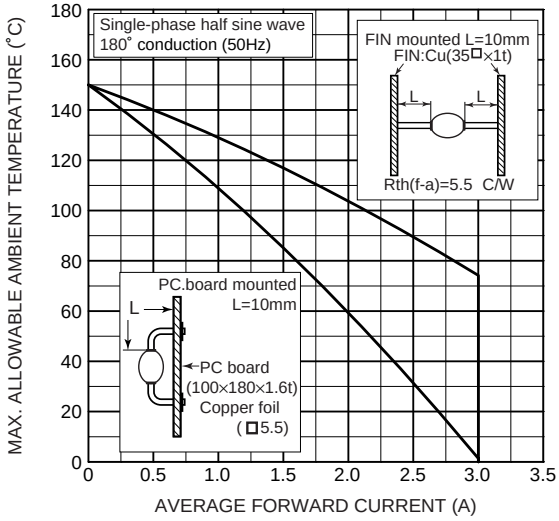
Forward characteristics



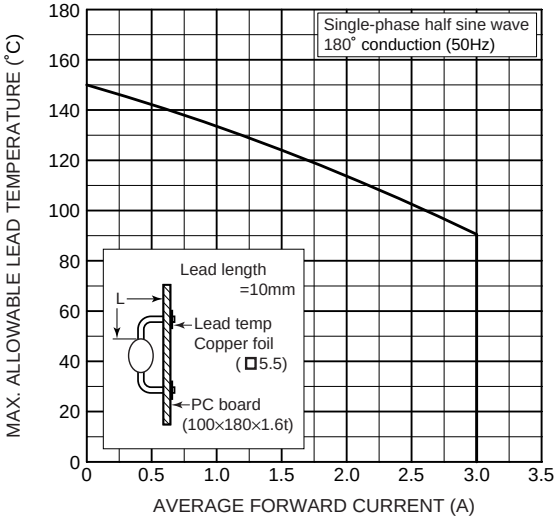
Max. average forward power dissipation
(Resistive or inductive load)



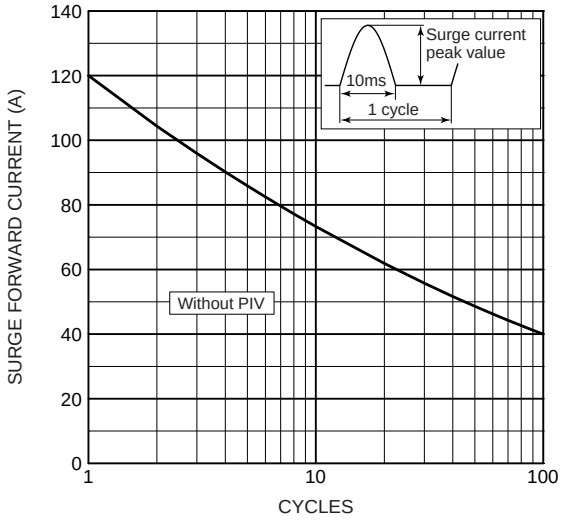
Max. allowable ambient temperature
(Resistive or inductive load)



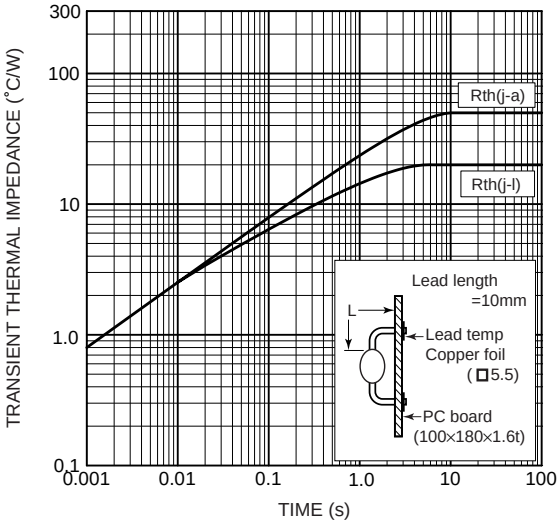
Max. allowable lead temperature
(Resistive or inductive load)



Surge forward current characteristic
(Non-repetitive)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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